

## **10A, 30V, 0.013 Ohm, N-Channel, Logic Level UltraFET Power MOSFET**



This N-Channel power MOSFET is manufactured using the innovative UltraFET process. This advanced process technology achieves the lowest possible on-resistance per silicon area, resulting in outstanding performance. This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching converters, motor drivers, relay drivers, low-voltage bus switches, and power management in portable and battery-operated products.

Formerly developmental type TA76131.

### **Ordering Information**

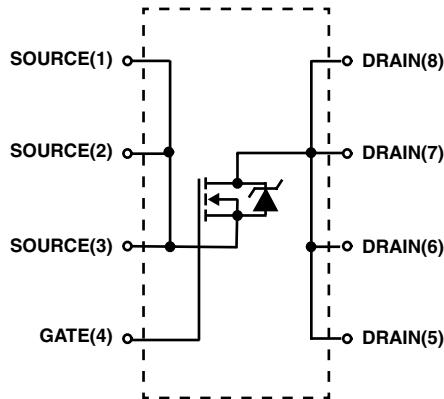
PART NUMBER	PACKAGE	BRAND
HUF76131SK8	MS-012AA	76131SK8

NOTE: When ordering, use the entire part number. Add the suffix T to obtain the variant in tape and reel, e.g., HUF76131SK8T.

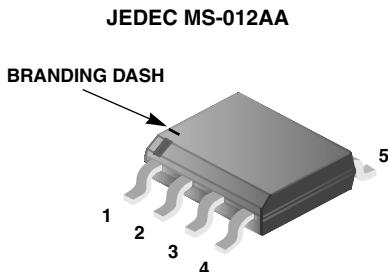
### **Features**

- Logic Level Gate Drive
- 10A, 30V
- Ultra Low On-Resistance,  $r_{DS(ON)} = 0.013\Omega$
- Temperature Compensating PSPICE® Model
- Thermal Impedance SPICE Model
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- Related Literature
  - TB334, "Guidelines for Soldering Surface Mount Components to PC Boards"

### **Symbol**



### **Packaging**



# HUF76131SK8

## Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ , Unless Otherwise Specified

		HUF76131SK8	UNITS
Drain to Source Voltage (Note 1).....	$V_{DSS}$	30	V
Drain to Gate Voltage ( $R_{GS} = 20\text{k}\Omega$ ) (Note 1).....	$V_{DGR}$	30	V
Gate to Source Voltage .....	$V_{GS}$	$\pm 16$	V
Drain Current			
Continuous (Figure 2) (Notes 2, 3).....	$I_D$	10	A
Pulsed Drain Current .....	$I_{DM}$	Figure 5	
Pulsed Avalanche Rating.....	$E_{AS}$	Figure 6	
Power Dissipation .....	$P_D$	2.5	W
Derate Above $25^\circ\text{C}$ .....		0.02	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature .....	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$
Maximum Temperature for Soldering			
Leads at 0.063in (1.6mm) from Case for 10s.....	$T_L$	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334.....	$T_{pkg}$	260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

### NOTE:

1.  $T_J = 25^\circ\text{C}$  to  $150^\circ\text{C}$ .

## Electrical Specifications $T_A = 25^\circ\text{C}$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
Drain to Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ (Figure 11)	30	-	-	V	
Gate to Source Threshold Voltage	$V_{GS(\text{TH})}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ (Figure 10)	1	-	-	V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$	
		$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, T_A = 150^\circ\text{C}$	-	-	250	$\mu\text{A}$	
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 16\text{V}$	-	-	$\pm 100$	nA	
Drain to Source On Resistance	$r_{DS(\text{ON})}$	$I_D = 10\text{A}, V_{GS} = 4.5\text{V}$ (Figures 9,14)	-	0.017	0.018	$\Omega$	
		$I_D = 10\text{A}, V_{GS} = 5\text{V}$	-	0.015	0.017	$\Omega$	
		$I_D = 10\text{A}, V_{GS} = 10\text{V}$	-	0.011	0.013	$\Omega$	
Turn-On Time	$t_{ON}$	$V_{DD} = 15\text{V}, I_D \geq 10\text{A}, R_L = 1.5\Omega, V_{GS} = 5\text{V}, R_{GS} = 6.8\Omega$ (Figure 15)	-	-	115	ns	
Turn-On Delay Time	$t_{d(\text{ON})}$		-	15	-	ns	
Rise Time	$t_r$		-	61	-	ns	
Turn-Off Delay Time	$t_{d(\text{OFF})}$		-	33	-	ns	
Fall Time	$t_f$		-	36	-	ns	
Turn-Off Time	$t_{OFF}$		-	-	105	ns	
Total Gate Charge	$Q_{g(\text{TOT})}$	$V_{GS} = 0\text{V}$ to $10\text{V}$	$V_{DD} = 15\text{V}, I_D \geq 10\text{A}, R_L = 1.5\Omega, I_g(\text{REF}) = 1.0\text{mA}$ (Figure 13)	-	39	47	nC
Gate Charge at $5\text{V}$	$Q_{g(5)}$	$V_{GS} = 0\text{V}$ to $5\text{V}$		-	22	26	nC
Threshold Gate Charge	$Q_{g(\text{TH})}$	$V_{GS} = 0\text{V}$ to $1\text{V}$		-	1.53	1.85	nC
Gate to Source Gate Charge	$Q_{gs}$	-		4.00	-	nC	
Gate to Drain "Miller" Charge	$Q_{gd}$	-		9.50	-	nC	
Input Capacitance	$C_{ISS}$	-		1605	-	pF	
Output Capacitance	$C_{OSS}$	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ (Figure 12)		-	685	-	pF
Reverse Transfer Capacitance	$C_{RSS}$			-	115	-	pF
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	Pad Area = $0.76 \text{ in}^2$ (Note 2)		-	-	50	$^\circ\text{C}/\text{W}$
		Pad Area = $0.054 \text{ in}^2$ (See TB377)		-	-	143.4	$^\circ\text{C}/\text{W}$
		Pad Area = $0.0115 \text{ in}^2$ (See TB377)		-	-	177.3	$^\circ\text{C}/\text{W}$

## Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	$V_{SD}$	$I_{SD} = 10\text{A}$	-	-	1.25	V
		$I_{SD} = 2.3\text{A}$	-	-	1.1	V
Reverse Recovery Time	$t_{rr}$	$I_{SD} = 2.3\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	57	ns
Reverse Recovered Charge	$Q_{RR}$	$I_{SD} = 2.3\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	81	nC

### NOTES:

2.  $50^\circ\text{C}/\text{W}$  measured using FR-4 board with  $0.76 \text{ in}^2$  footprint at 10 seconds.
3.  $177.3^\circ\text{C}/\text{W}$  measured using FR-4 board with  $0.0115 \text{ in}^2$  footprint at 1000 seconds.

## Typical Performance Curves

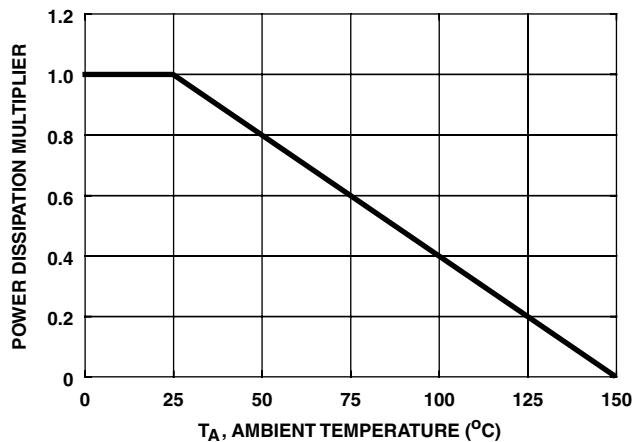


FIGURE 1. NORMALIZED POWER DISSIPATION vs AMBIENT TEMPERATURE

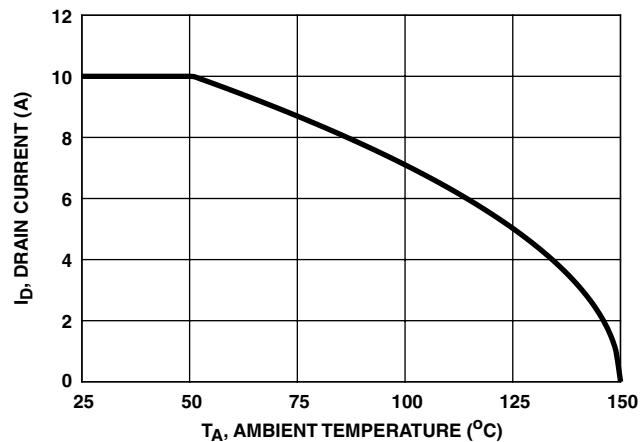


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs AMBIENT TEMPERATURE

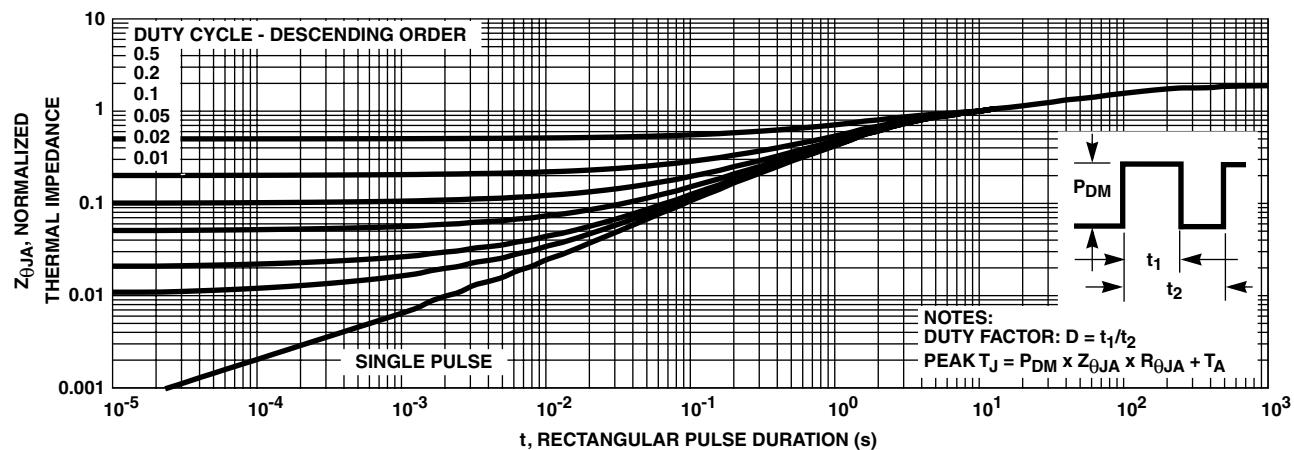


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

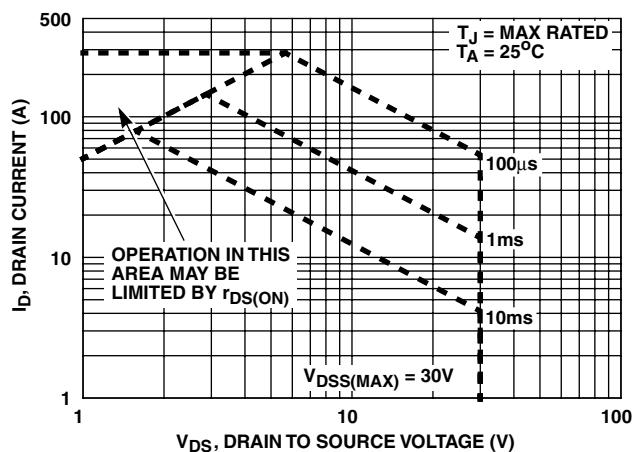


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

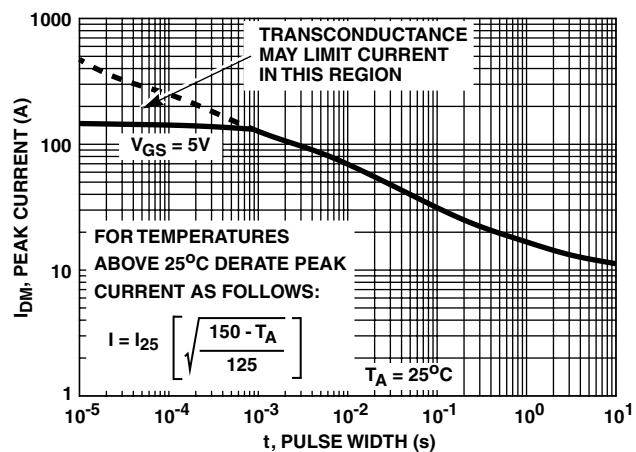
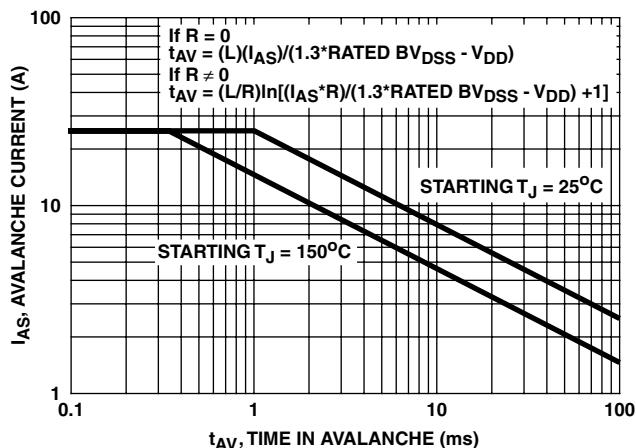
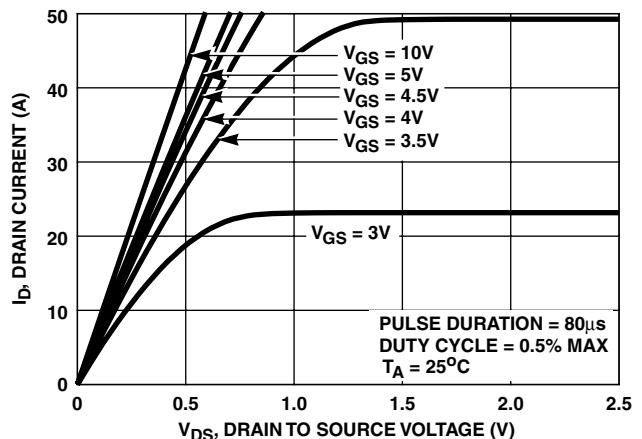


FIGURE 5. PEAK CURRENT CAPABILITY

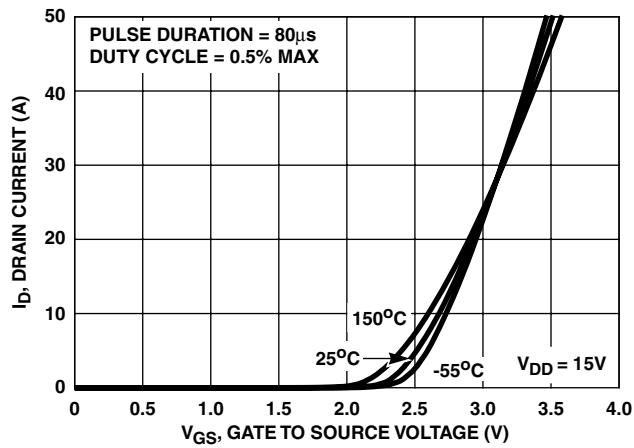
**Typical Performance Curves (Continued)**

NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

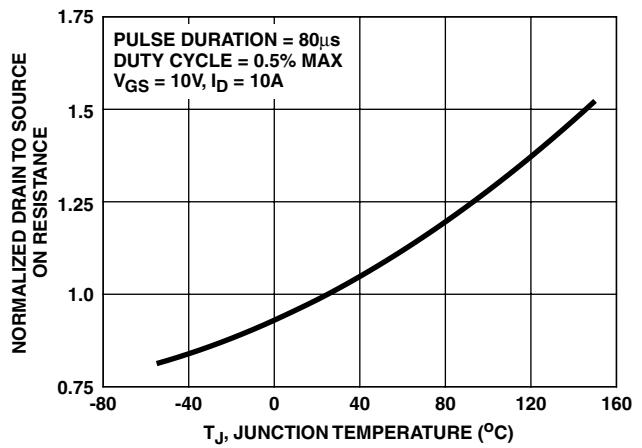
**FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY**



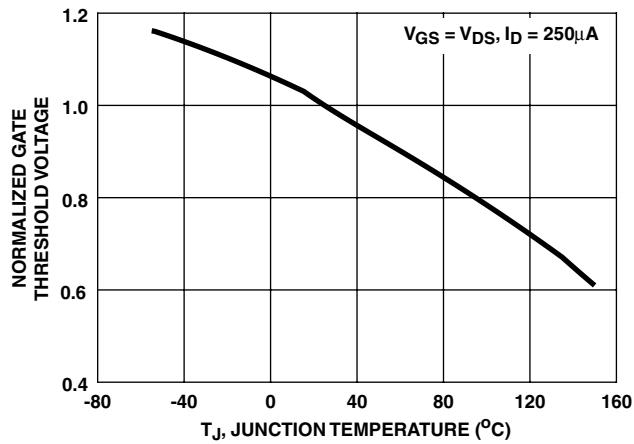
**FIGURE 7. SATURATION CHARACTERISTICS**



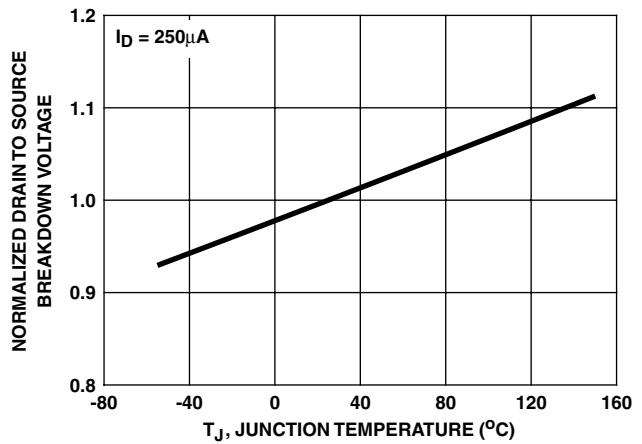
**FIGURE 8. TRANSFER CHARACTERISTICS**



**FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE**



**FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE**



**FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE**

**Typical Performance Curves (Continued)**

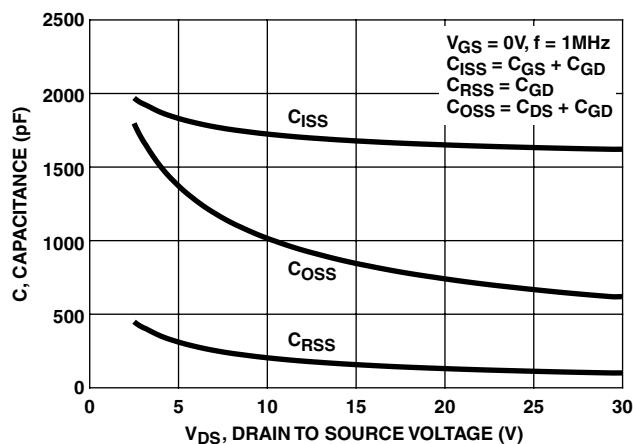
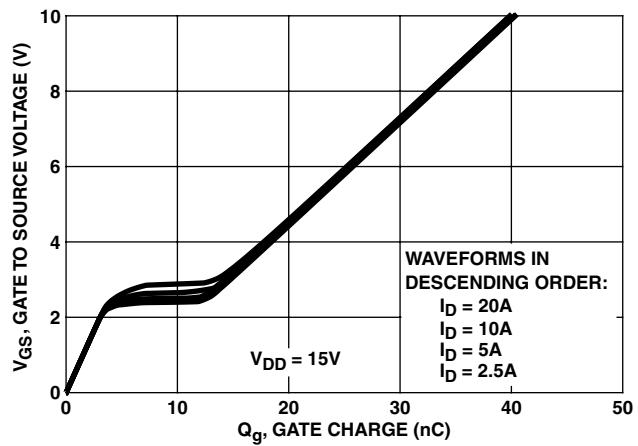


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes 7254 and 7260.

FIGURE 13. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

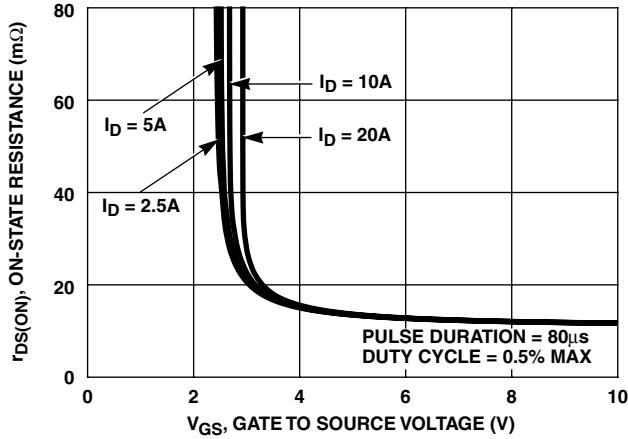


FIGURE 14. DRAIN TO SOURCE ON-STATE RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

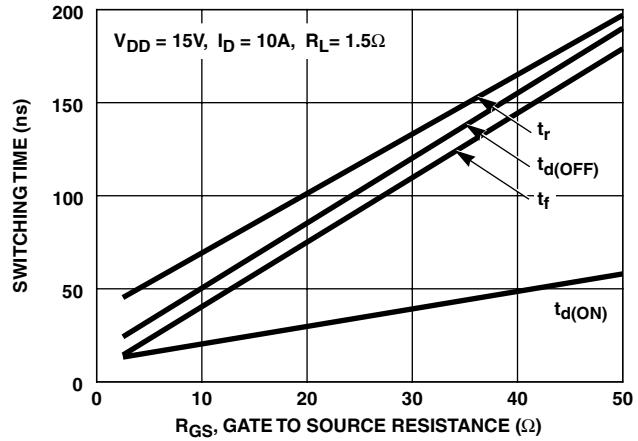


FIGURE 15. SWITCHING TIME vs GATE RESISTANCE

**Test Circuits and Waveforms**

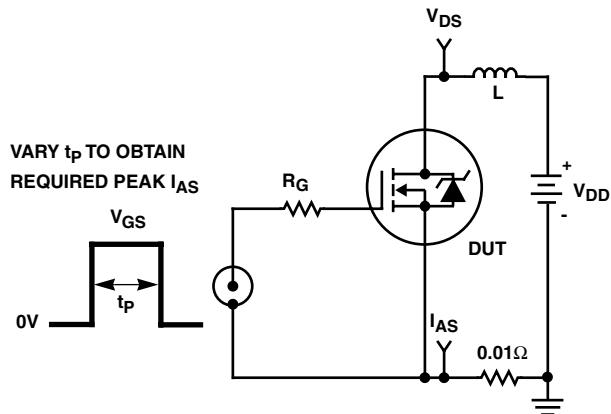


FIGURE 16. UNCLAMPED ENERGY TEST CIRCUIT

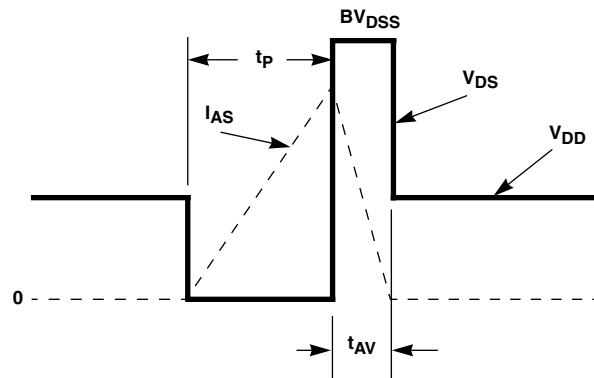


FIGURE 17. UNCLAMPED ENERGY WAVEFORMS

**Test Circuits and Waveforms (Continued)**

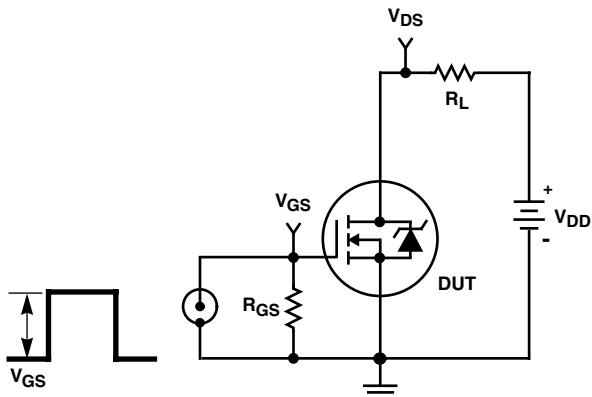


FIGURE 18. SWITCHING TIME TEST CIRCUIT

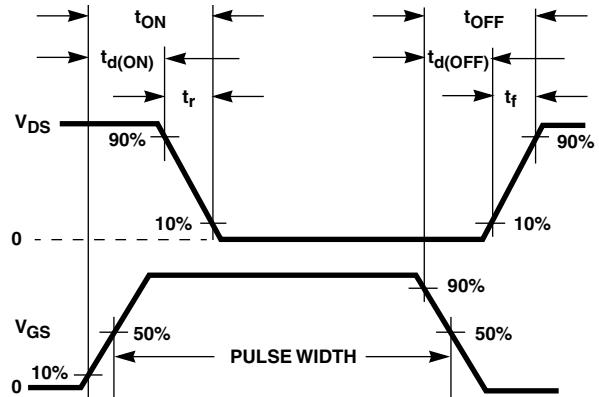


FIGURE 19. SWITCHING TIME WAVEFORM

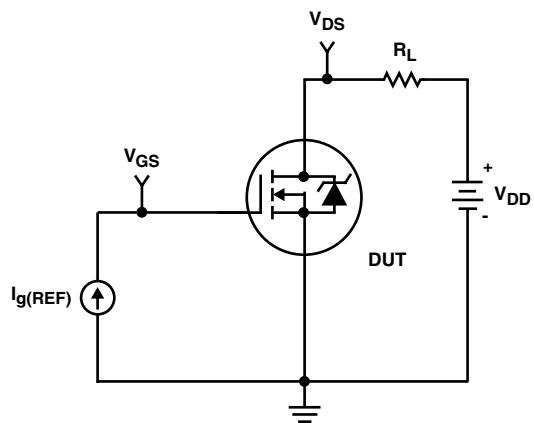


FIGURE 20. GATE CHARGE TEST CIRCUIT

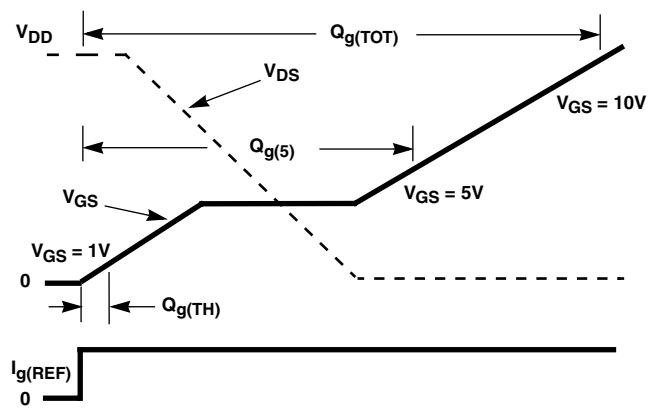


FIGURE 21. GATE CHARGE WAVEFORMS

## Thermal Resistance vs Mounting Pad Area

The maximum rated junction temperature  $T_{JMAX}$  constrains the maximum allowable device power dissipation  $P_{Dmax}$  in an application. The application ambient temperature  $T_A$  ( $^{\circ}$ C) and thermal impedance  $Z_{\theta JA}$  ( $^{\circ}$ C/W) must be reviewed to ensure that  $T_{JMAX}$  ( $^{\circ}$ C) is never exceeded. Equation 1 mathematically represents the relationship.

$$P_{Dmax} = \frac{(T_{JMAX} - T_A)}{Z_{\theta JA}} \quad (\text{EQ. 1})$$

Fairchild provides thermal information to assist the designer's preliminary application evaluation. Precise determination of  $P_{Dmax}$  is complex and influenced by many factors:

1. PC heat sink area and location (top and bottom), copper leads and mounting pad area.
2. Air Flow, board orientation and type.
3. Power pulse width and duty factor.

Figure 22 addresses these points by depicting  $R_{\theta JA}$  values vs. top copper (component side) heat sink area. The measurements were performed in still air using a horizontally positioned FR-4 board with 1oz copper after 1000 seconds of steady state power.

Figure 22 also displays the two  $R_{\theta JA}$  values listed in the Electrical Specifications table. The two points were chosen to graphically depict the compromise between copper board area, thermal resistance and ultimately power dissipation.

Thermal resistance values corresponding to other component side copper areas can be obtained from Figure 22 or by calculation using Equation 2. Area in Equation 2 is the top copper area including the gate and source pads.

$$R_{\theta JA} = 79.3 - 21.8 \times \ln(\text{Area}) \quad (\text{EQ. 2})$$

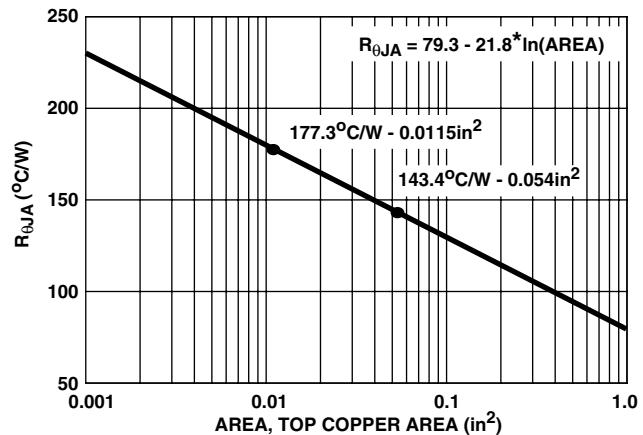


FIGURE 22. THERMAL RESISTANCE vs MOUNTING PAD AREA

Figure 22 provides the necessary information for steady state junction temperature or power dissipation calculations. Transient pulse applications are best studied using the Fairchild device SPICE thermal model.

## PSPICE Electrical Model

SUBCKT HUF76131 2 1 3 ; rev 12/31/97

CA 12 8 2.22-9  
 CB 15 14 2.13e-9  
 CIN 6 8 1.52e-9

DBODY 7 5 DBODYMOD  
 DBREAK 5 11 DBREAKMOD  
 DPLCAP 10 5 DPLCAPMOD

EBREAK 11 7 17 18 37.4  
 EDS 14 8 5 8 1  
 EGS 13 8 6 8 1  
 ESG 6 10 6 8 1  
 EVTHRES 6 21 19 8 1  
 EVTEMP 20 6 18 22 1

IT 8 17 1

LDRAIN 2 5 1e-9  
 LGATE 1 9 1.04e-9  
 LSOURCE 3 7 1.29e-10

MMED 16 6 8 8 MMEDMOD  
 MSTRO 16 6 8 8 MSTROMOD  
 MWEAK 16 21 8 8 MWEAKMOD

RBREAK 17 18 RBREAKMOD 1  
 RDRAIN 50 16 RDRAINMOD 1.94e-3  
 RGATE 9 20 2.20  
 RLDRAIN 2 5 10  
 RLGATE 1 9 10.4  
 RLSOURCE 3 7 1.29  
 RSLC1 5 51 RSLCMOD 1e-6  
 RSLC2 5 50 1e3  
 RSOURCE 8 7 RSOURCEMOD 8.75e-3  
 RVTHRES 22 8 RVTHRESMOD 1  
 RVTEMP 18 19 RVTEMPPMOD 1

S1A 6 12 13 8 S1AMOD  
 S1B 13 12 13 8 S1BMOD  
 S2A 6 15 14 13 S2AMOD  
 S2B 13 15 14 13 S2BMOD

VBAT 22 19 DC 1

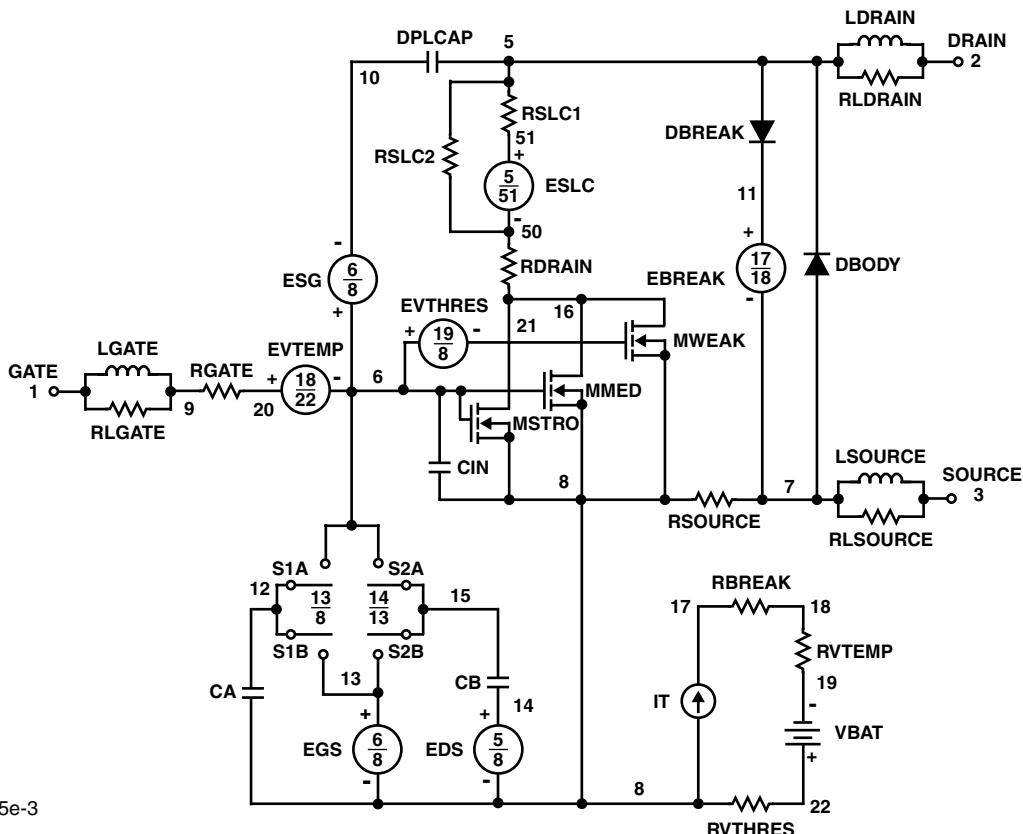
ESLC 51 50 VALUE={(V(5,51)/ABS(V(5,51)))\*(PWR(V(5,51)/(1e-6\*275),3))}

.MODEL DBODYMOD D (IS = 2.25e-12 RS = 6.05e-3 IKF=16.00 TRS1 = 1.14e-4 TRS2 = 1.23e-6 CJO = 2.35e-9 TT = 2.71e-8 M = 0.44)  
 .MODEL DBREAKMOD D (RS = 1.05e-1 TRS1 = 1.01e-4 TRS2 = 1.11e-7)  
 .MODEL DPLCAPMOD D (CJO = 1.08e-9 IS = 1e-30 N = 10 M = 0.69)  
 .MODEL MMEDMOD NMOS (VTO = 1.89 KP = 5.05 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 2.20)  
 .MODEL MSTROMOD NMOS (VTO = 2.22 KP = 125.00 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u)  
 .MODEL MWEAKMOD NMOS (VTO = 1.62 KP = 0.10 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 22.0 RS = 0.1)  
 .MODEL RBREAKMOD RES (TC1 = 9.54e-4 TC2 = 1.07e-7)  
 .MODEL RDRAINMOD RES (TC1 = 1.61e-2 TC2 = 5.17e-5)  
 .MODEL RSLCMOD RES (TC1 = 1.03e-5 TC2 = 7.67e-7)  
 .MODEL RSOURCEMOD RES (TC1 = 0 TC2 = 0)  
 .MODEL RVTHRESMOD RES (TC = -2.81e-3 TC2 = -8.75e-6)  
 .MODEL RVTEMPPMOD RES (TC1 = -6.68e-4 TC2 = 8.80e-7)

.MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -5.80 VOFF= -1.50)  
 .MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -1.50 VOFF= -5.80)  
 .MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -0.50 VOFF= -0.00)  
 .MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 0.00 VOFF= -0.50)

.ENDS

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.



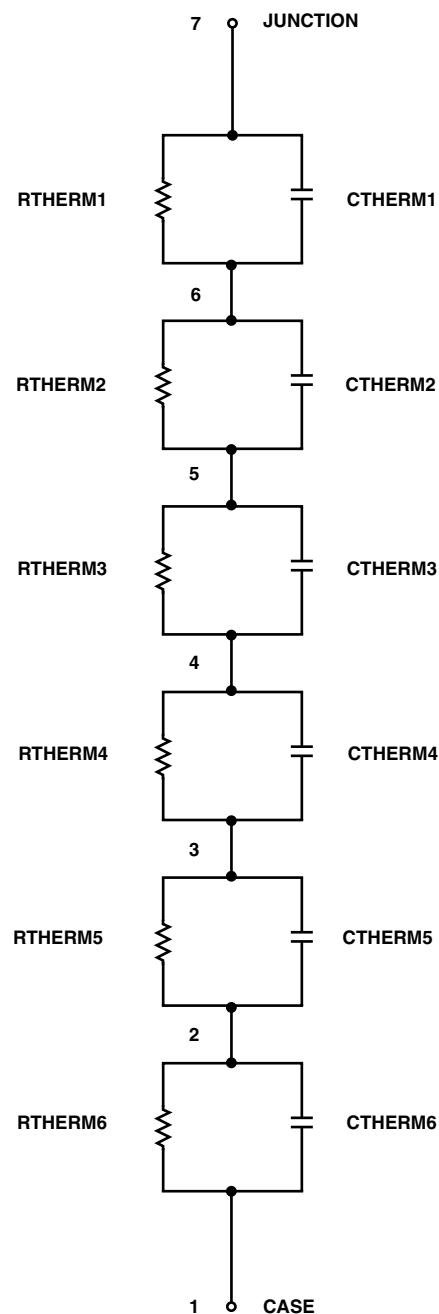
**SPICE Thermal Model**

REV 20 Feb 98

HUF76131

CTHERM1 7 6 3.75e-4  
CTHERM2 6 5 3.05e-3  
CTHERM3 5 4 3.70e-2  
CTHERM4 4 3 2.52e-2  
CTHERM5 3 2 8.50e-2  
CTHERM6 2 1 7.95e-1

RTERM1 7 6 3.95e-2  
RTERM2 6 5 2.50e-1  
RTERM3 5 4 4.00e-1  
RTERM4 4 3 6.35  
RTERM5 3 2 2.02e1  
RTERM6 2 1 4.80e1



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CoolFET <sup>TM</sup>	FRFET <sup>TM</sup>	PACMAN <sup>TM</sup>	Stealth <sup>TM</sup>	
CROSSVOLT <sup>TM</sup>	GlobalOptoisolator <sup>TM</sup>	POP <sup>TM</sup>	SuperSOT <sup>TM</sup> -3	
DenseTrench <sup>TM</sup>	GTOT <sup>TM</sup>	Power247 <sup>TM</sup>	SuperSOT <sup>TM</sup> -6	
DOME <sup>TM</sup>	HiSeC <sup>TM</sup>	PowerTrench <sup>®</sup>	SuperSOT <sup>TM</sup> -8	
EcoSPARK <sup>TM</sup>	ISOPLANAR <sup>TM</sup>	QFET <sup>TM</sup>	SyncFET <sup>TM</sup>	
E <sup>2</sup> CMOS <sup>TM</sup>	LittleFET <sup>TM</sup>	QS <sup>TM</sup>	TinyLogic <sup>TM</sup>	
EnSigna <sup>TM</sup>	MicroFET <sup>TM</sup>	QT Optoelectronics <sup>TM</sup>	TruTranslation <sup>TM</sup>	
FACT <sup>TM</sup>	MicroPak <sup>TM</sup>	Quiet Series <sup>TM</sup>	UHC <sup>TM</sup>	
FACT Quiet Series <sup>TM</sup>	MICROWIRE <sup>TM</sup>	SILENT SWITCHER <sup>®</sup>	UltraFET <sup>®</sup>	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.